COMPLEMENTARY PAIR SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

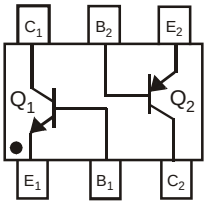
Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.003 grams (approximate)

SOT563

Top View

Bottom View



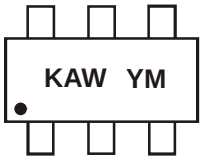
Device Schematic
Top View

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BC847BVN-7	KAW	7	8	3000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



KAW = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: Y = 2011)
M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings: NPN, BC847B Type (Q_1) (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Peak Emitter Current	I_{EM}	200	mA

Maximum Ratings: PNP, BC857B Type (Q_2) (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-100	mA
Peak Collector Current	I_{CM}	-200	mA
Peak Emitter Current	I_{EM}	-200	mA

Thermal Characteristics – Total Device (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Total Device	P_D	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Note: 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

Thermal Characteristics – Total Device

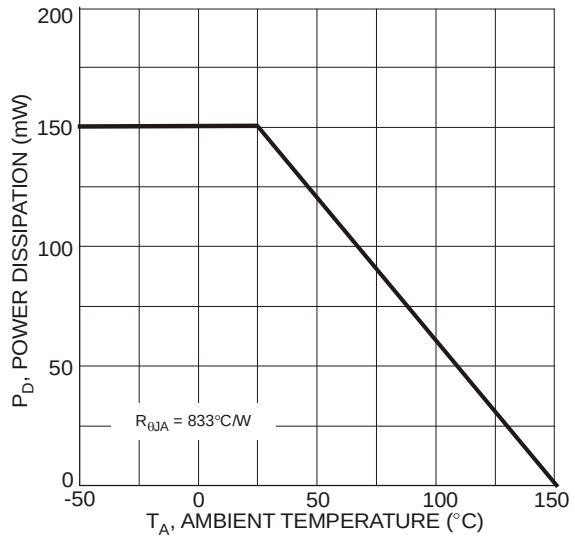


Figure 1. Power Dissipation vs. Ambient Temperature
Total Device

Electrical Characteristics: NPN, BC847B Type (Q_1) (@T_A = +25°C unless otherwise specified.)

Characteristic (Note 6)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	I_C = 100µA, I_B = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	45	—	—	V	I_C = 10mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	6	—	—	V	I_E = 100µA, I_C = 0
DC Current Gain	h_{FE}	200	290	450	—	V_{CE} = 5.0V, I_C = 2.0mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	— —	90 200	250 600	mV	I_C = 10mA, I_B = 0.5mA I_C = 100mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	700 900	—	mV	I_C = 10mA, I_B = 0.5mA I_C = 100mA, I_B = 5.0mA
Base-Emitter Voltage	$V_{BE(on)}$	580 —	660 —	700 720	mV	V_{CE} = 5.0V, I_C = 2.0mA V_{CE} = 5.0V, I_C = 10mA
Collector-Cutoff Current	I_{CBO}	— —	— —	15 5.0	nA µA	V_{CB} = 30V V_{CB} = 30V, T_A = +150°C
Gain Bandwidth Product	f_T	100	300	—	MHz	V_{CE} = 5.0V, I_C = 10mA, f = 100MHz
Collector-Base Capacitance	C_{CBO}	—	3.5	6.0	pF	V_{CB} = 10V, f = 1.0MHz

Notes: 6. Short duration pulse test used to minimize self-heating effect.

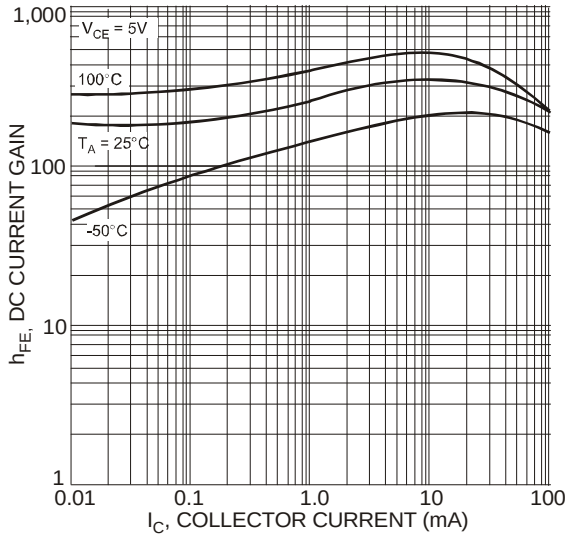


Figure 2. Typical DC Current Gain vs. Collector Current (BC847B Type)

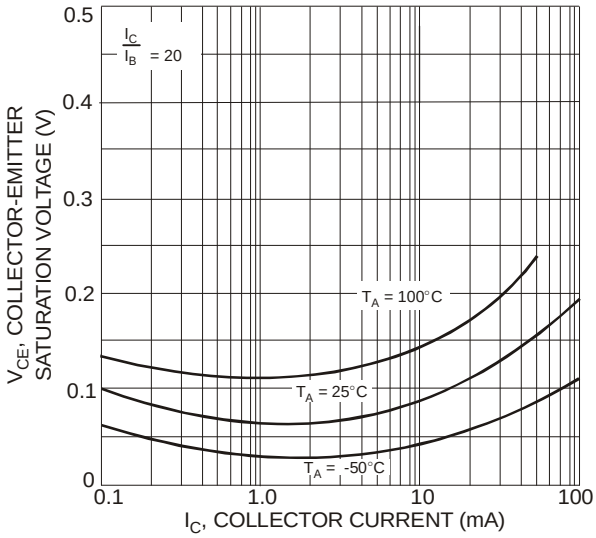


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC847B Type)

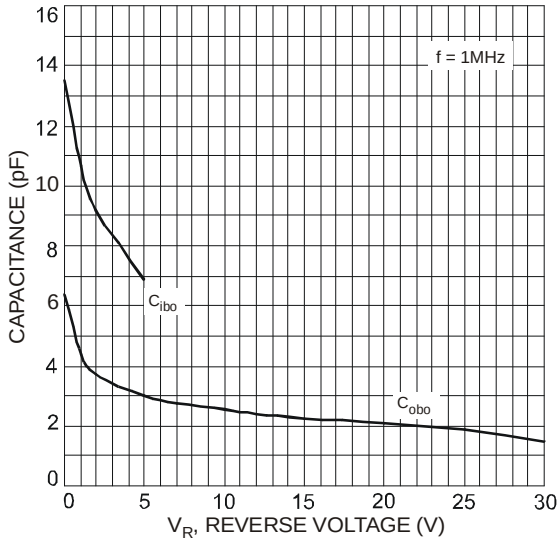


Figure 4. Typical Capacitance Characteristics (BC847B Type)

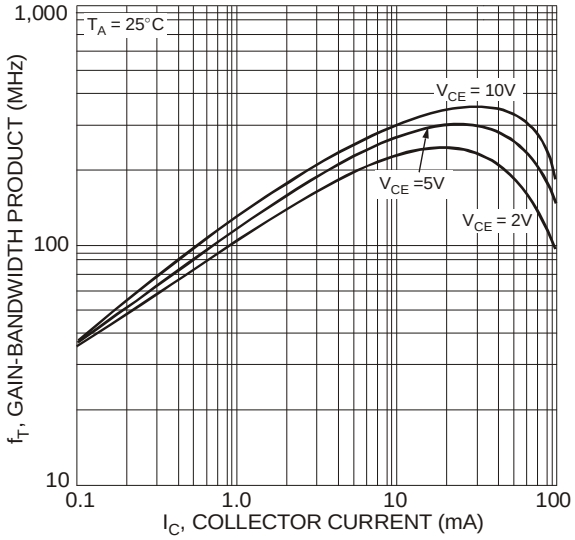


Figure 5. Typical Gain-Bandwidth Product vs. Collector Current (BC847B Type)

Electrical Characteristics: PNP, BC857B Type (Q_2) (@T_A = +25°C unless otherwise specified.)

Characteristic (Note 6)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-50	—	—	V	I_C = -100µA, I_B = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-45	—	—	V	I_C = -10mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	-6	—	—	V	I_E = -100µA, I_C = 0
DC Current Gain	h_{FE}	220	290	475	—	V_{CE} = -5.0V, I_C = -2.0mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-75 -250	-300 -650	mV	I_C = -10mA, I_B = -0.5mA I_C = -100mA, I_B = -5.0mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	-700 -850	— -950	mV	I_C = -10mA, I_B = -0.5mA I_C = -100mA, I_B = -5.0mA
Base-Emitter Voltage	$V_{BE(on)}$	-600 —	-650 —	-750 -820	mV	V_{CE} = -5.0V, I_C = -2.0mA V_{CE} = -5.0V, I_C = -10mA
Collector-Cutoff Current	I_{CBO}	— —	— —	-15 -4.0	nA µA	V_{CB} = -30V V_{CB} = -30V, T_A = +150°C
Gain Bandwidth Product	f_T	100	200	—	MHz	V_{CE} = -5.0V, I_C = -10mA, f = 100MHz
Collector-Base Capacitance	C_{CBO}	—	3	4.5	pF	V_{CB} = -10V, f = 1.0MHz

Notes: 6. Short duration pulse test used to minimize self-heating effect.

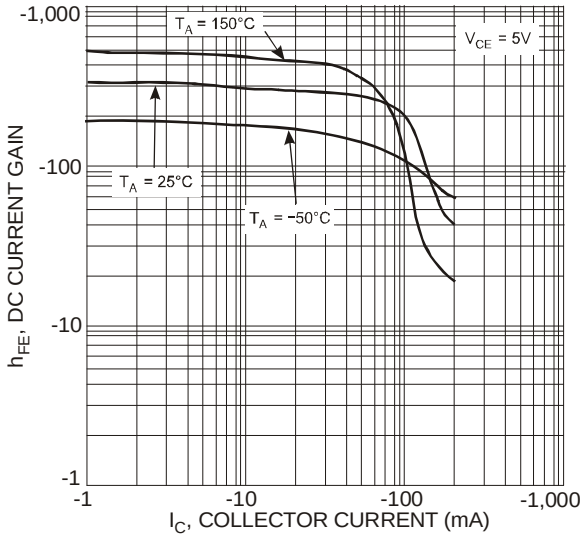


Figure 6. Typical DC Current Gain vs. Collector Current (BC857B Type)

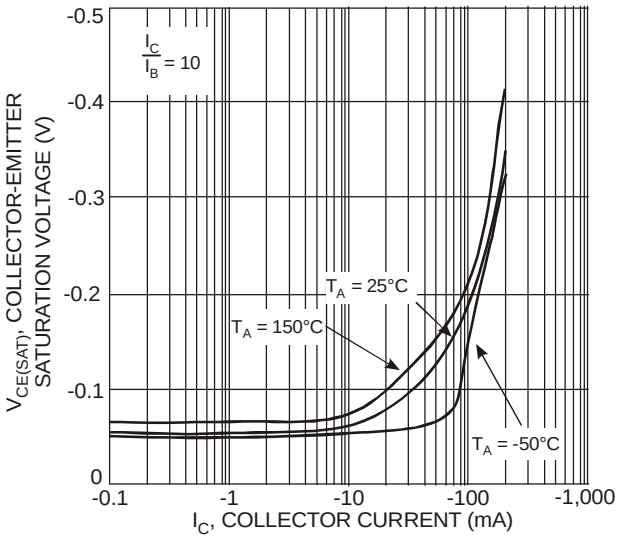


Figure 7. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC857B Type)

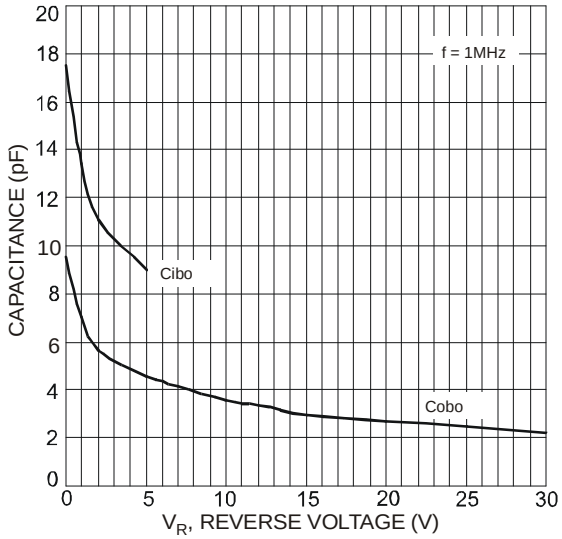


Figure 8. Typical Capacitance Characteristics (BC857B Type)

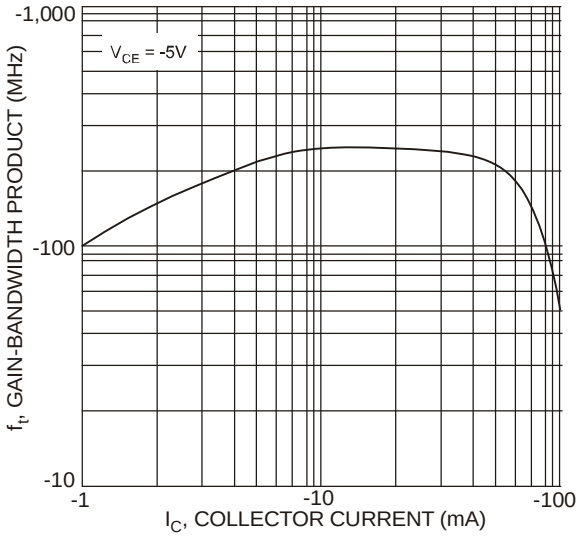
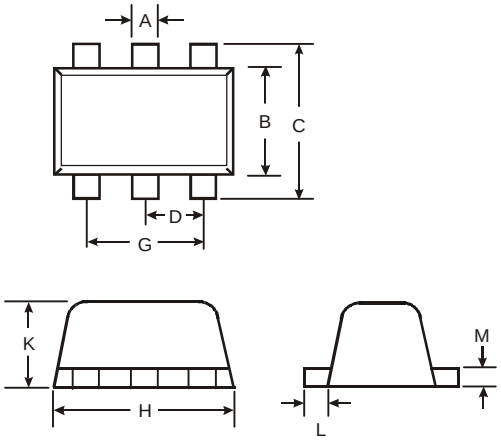


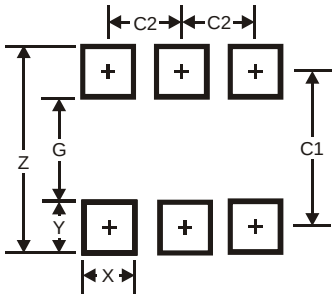
Figure 9. Typical Gain-Bandwidth Product vs. Collector Current (BC857B Type)

Package Outline Dimensions



SOT563			
Dim	**Min**	**Max**	**Typ**
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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